

**IN THE CLAIMS**

Claims 1-9 (Canceled).

10 (Original). An integrated circuit comprising:

a semiconductor structure;  
a first trench formed of a first depth in said semiconductor structure;  
a covering on said first trench and over said semiconductor structure, said covering being thicker in said first trench than over said semiconductor structure; and  
said covering having an opening to define a region for a second trench.

11 (Original). The circuit of claim 10 wherein said covering is spin-on glass.

Claims 12-15 (Canceled).

16 (New). The circuit of claim 10 wherein said opening is a trench.

17 (New). The circuit of claim 16 wherein said opening extends transversely to said first trench.